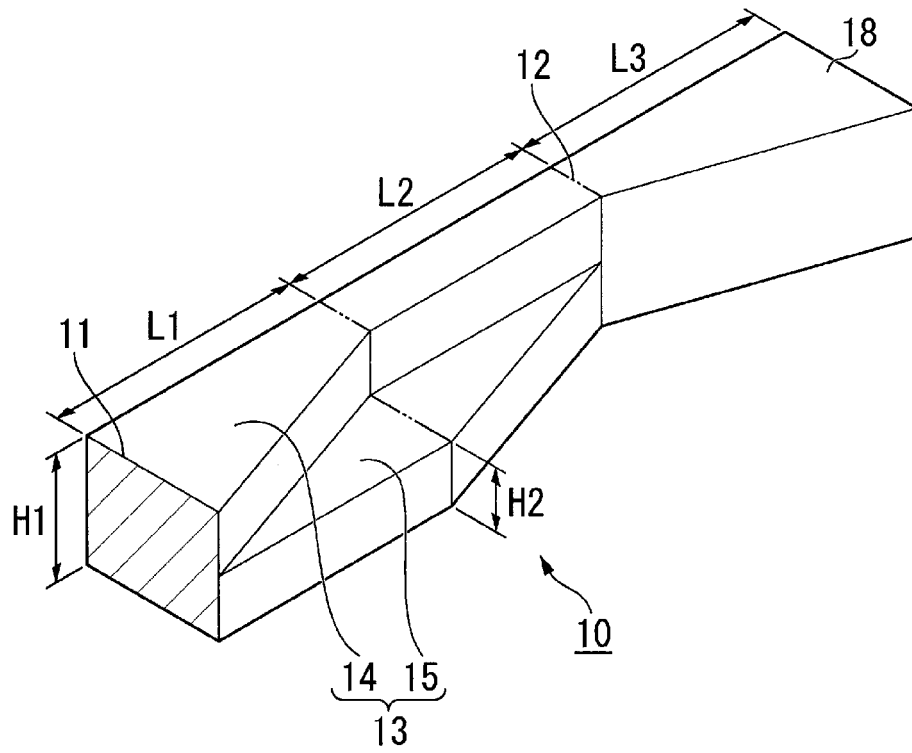
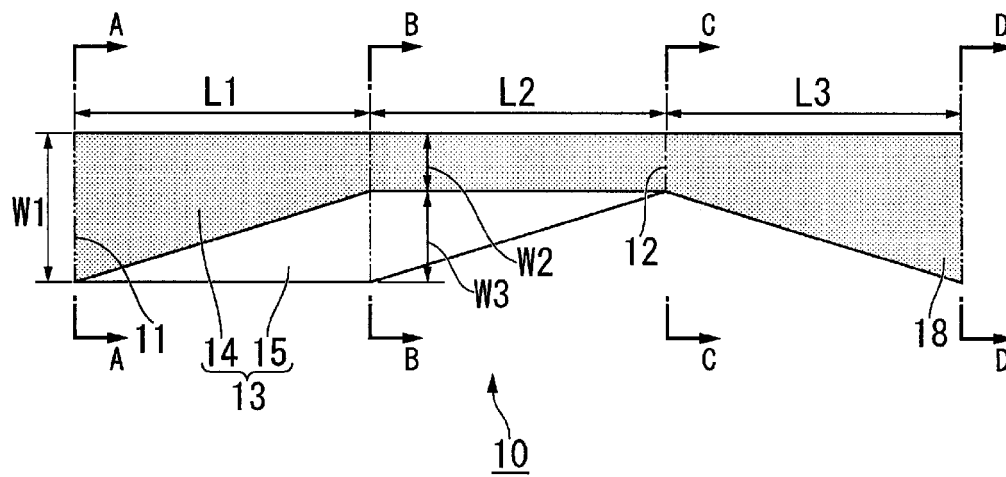


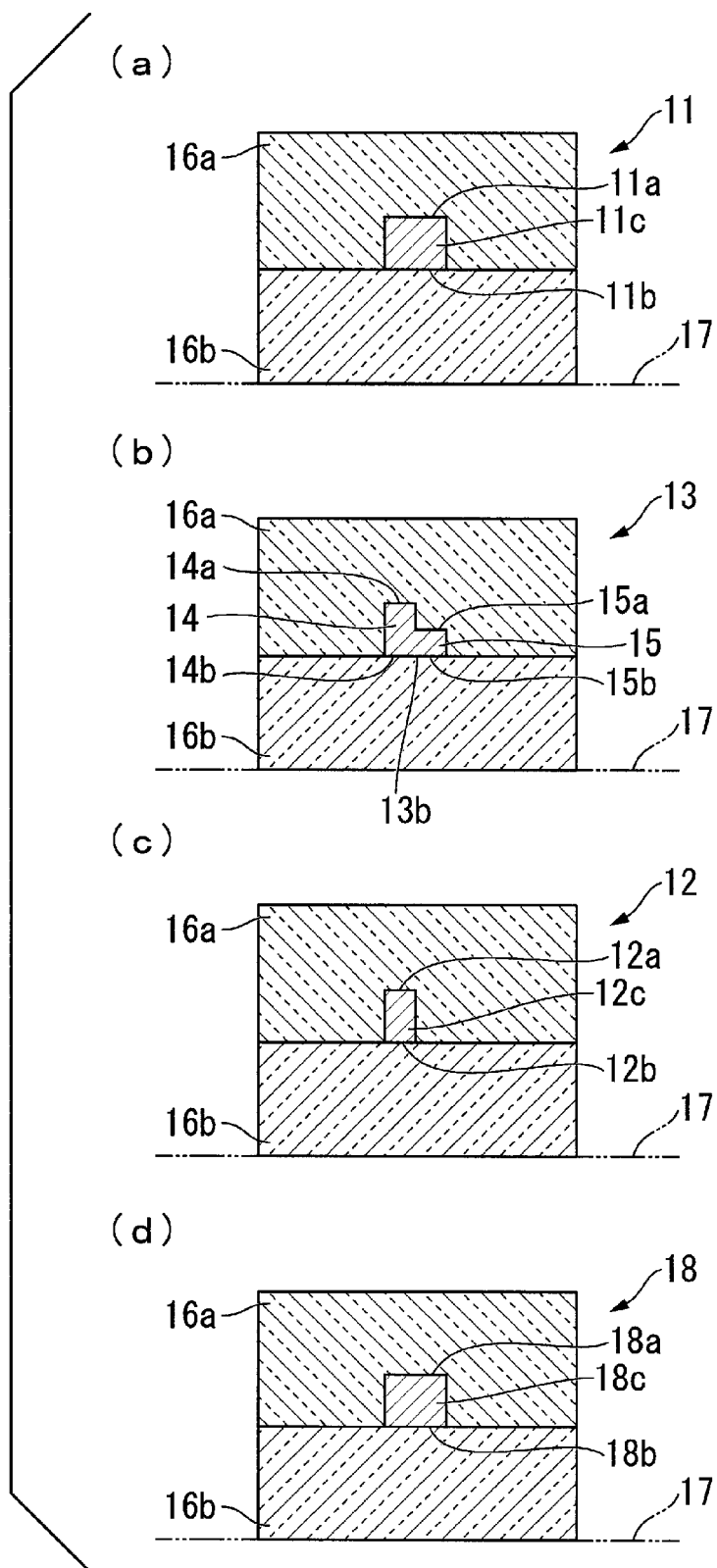
[図1]



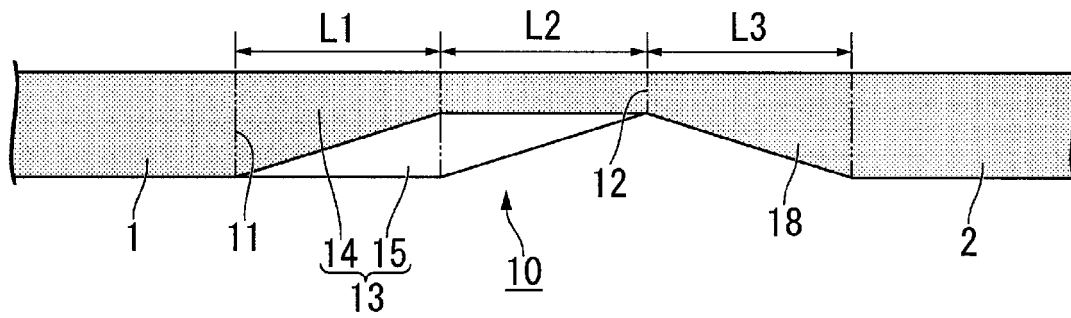
[図2]



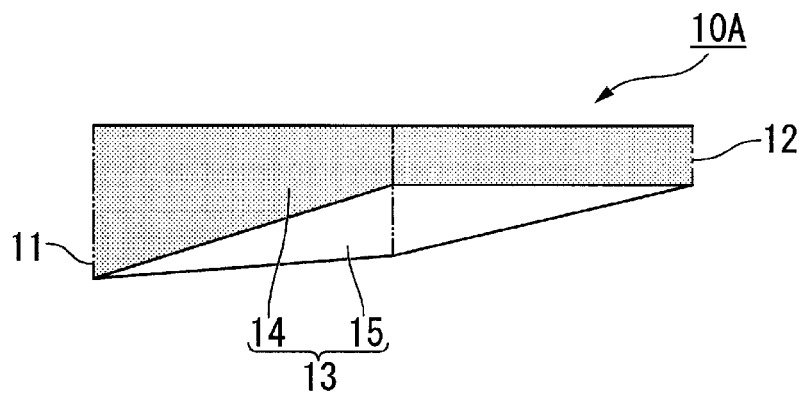
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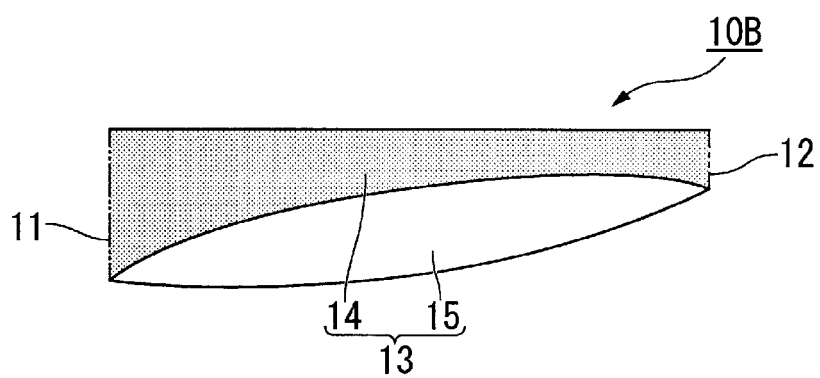
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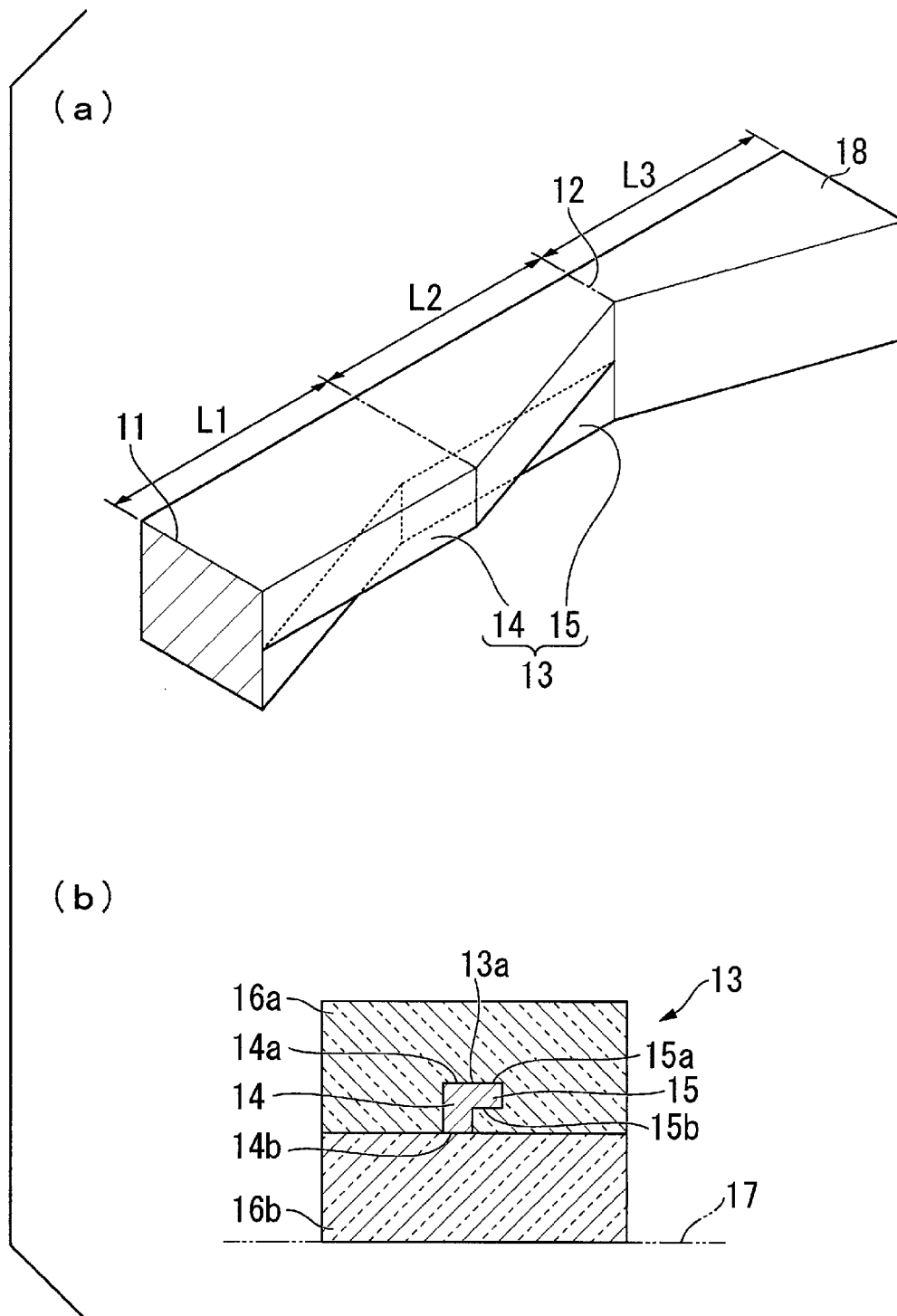
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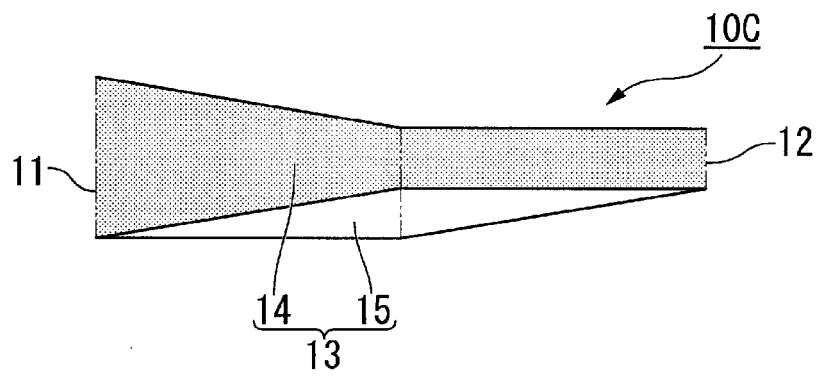
[図6]



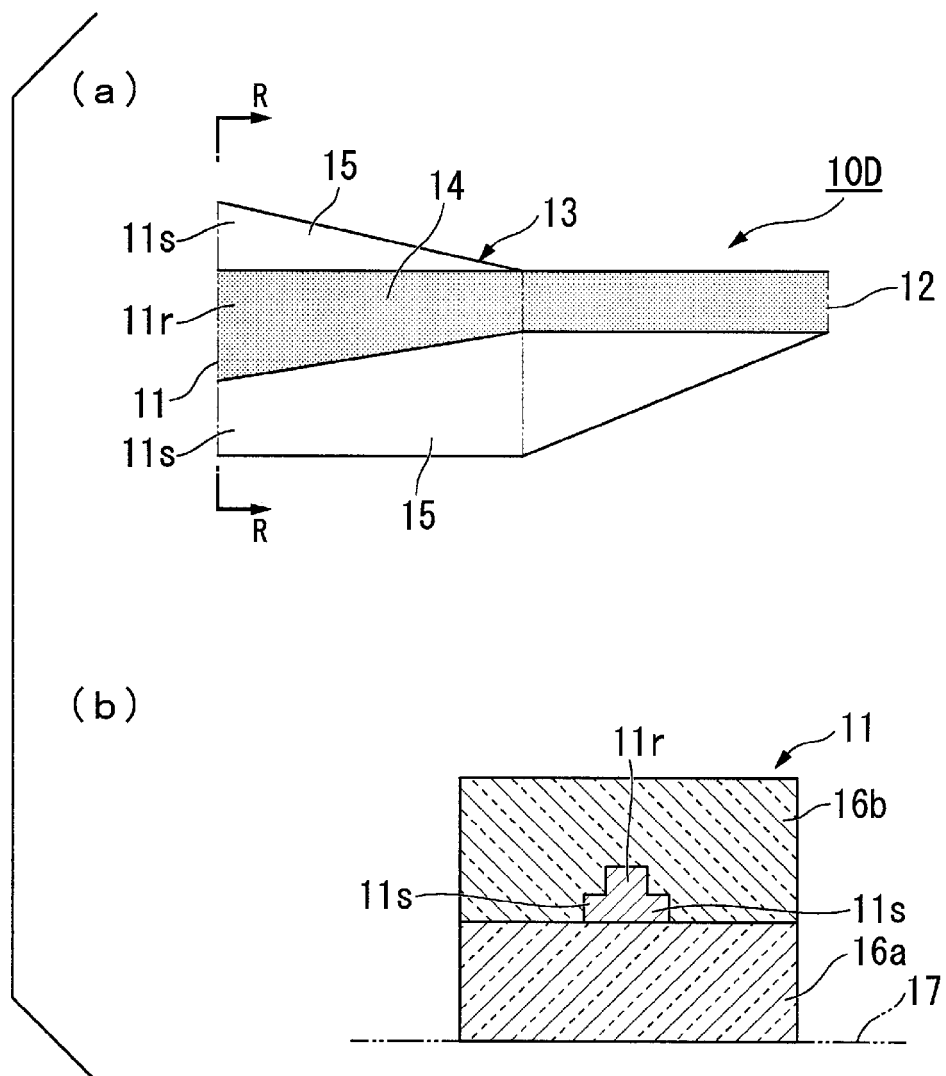
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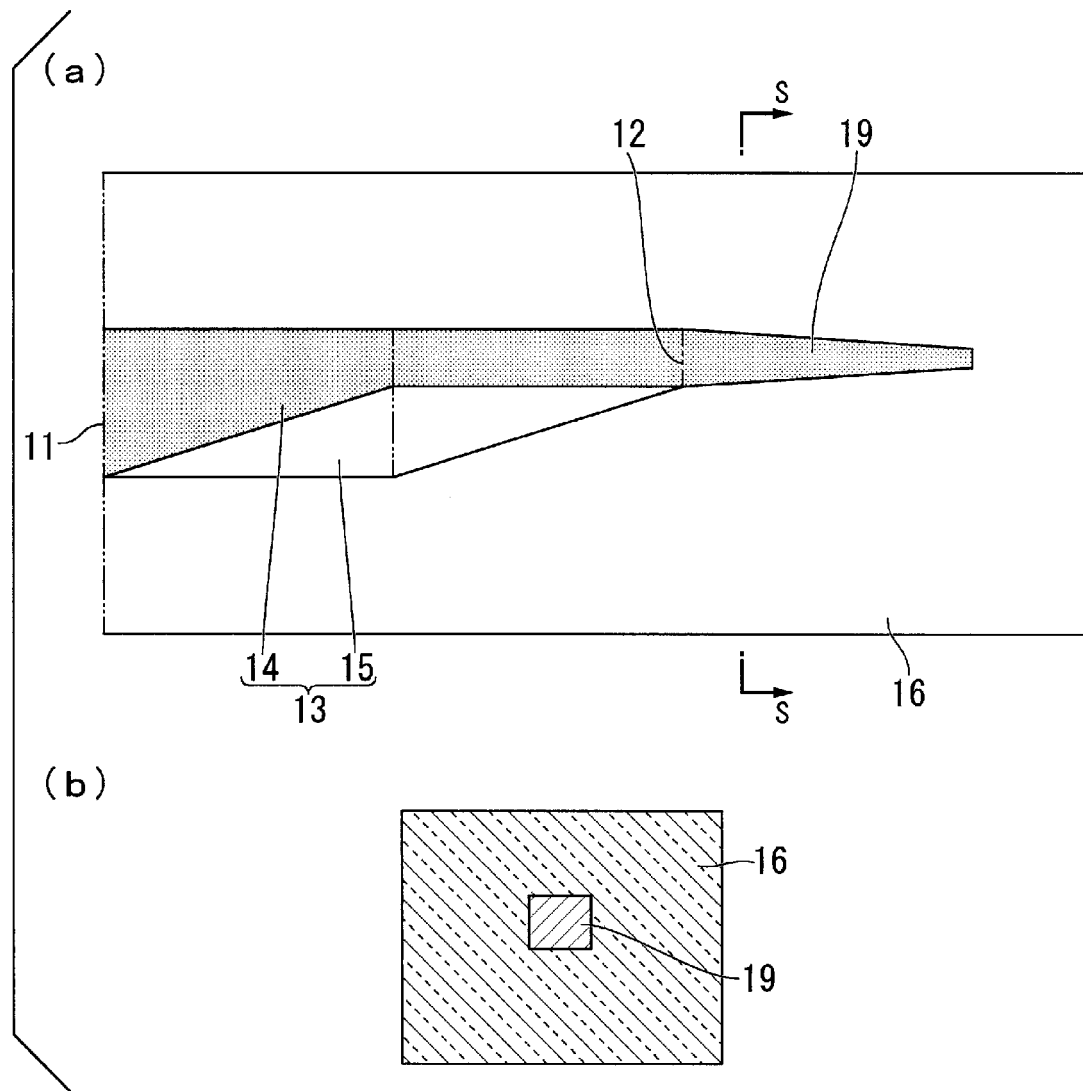
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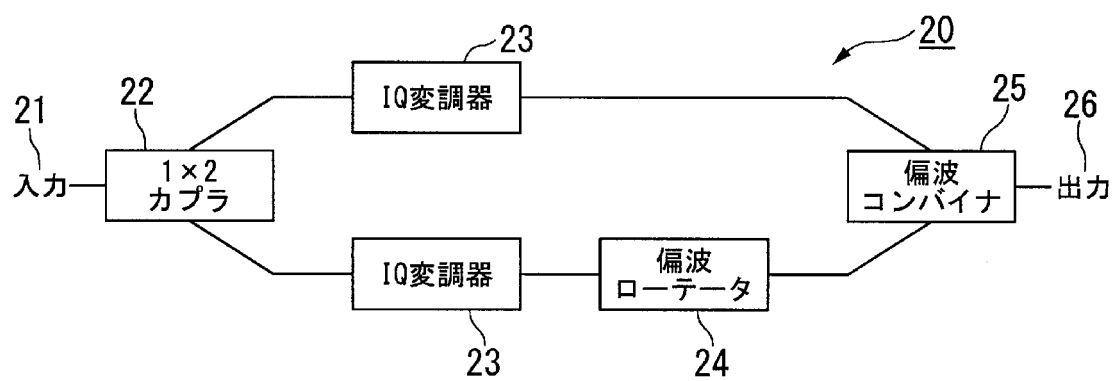
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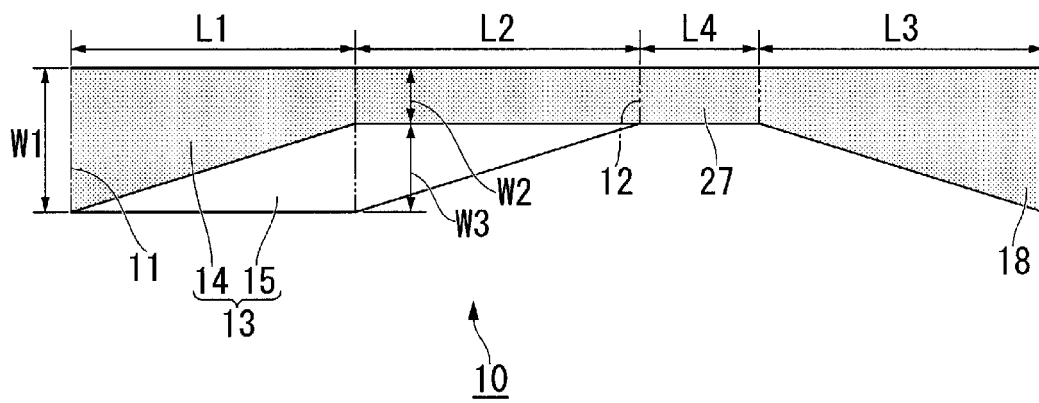
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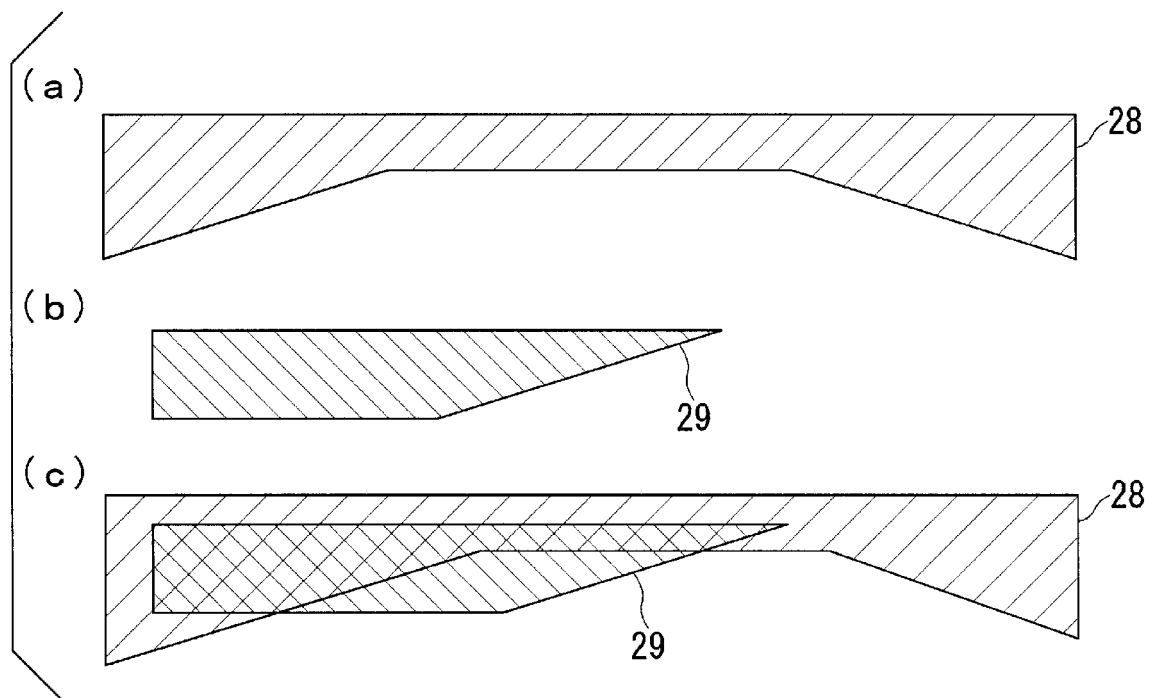
[図11]



[図12]



[図13]



[図14]

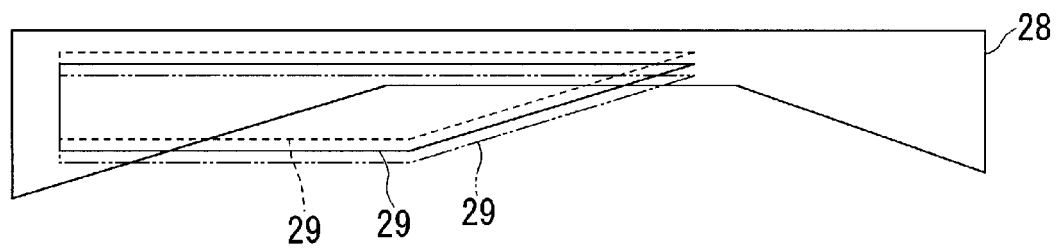
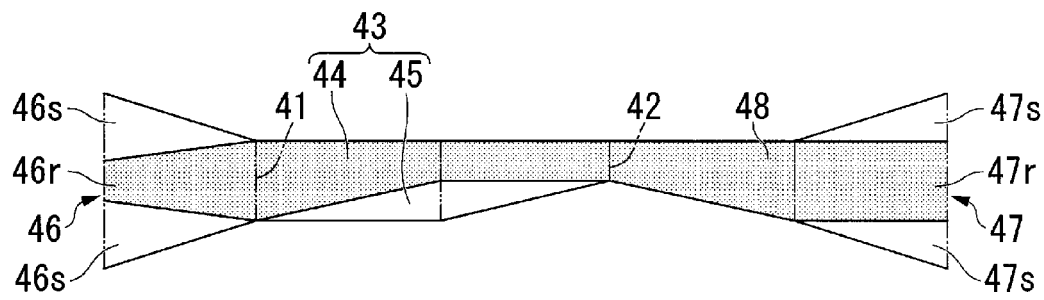
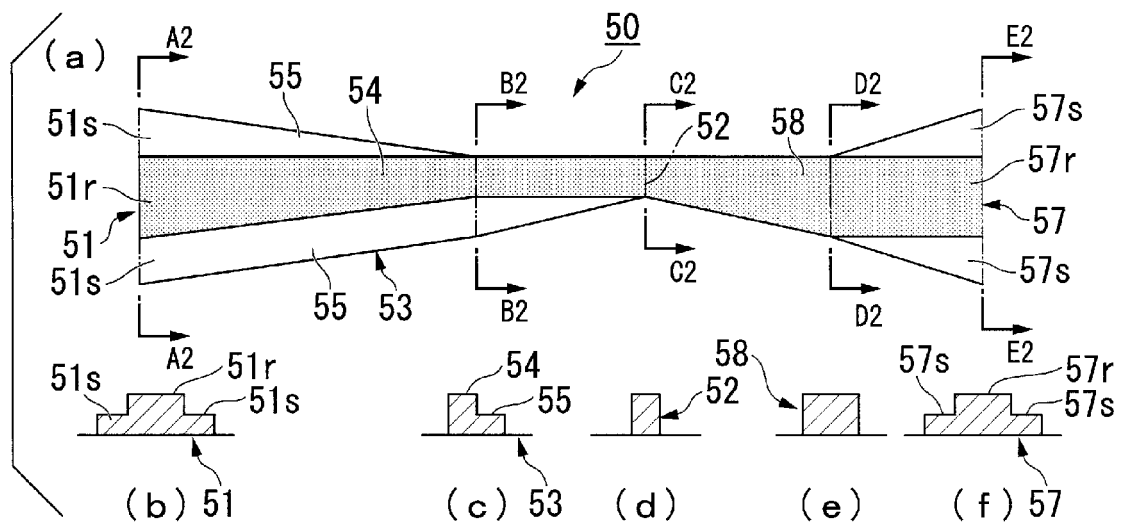


Figure 1 is a cross-sectional view of a semiconductor device. It shows a substrate 33 with a concave surface 35. Three rectangular regions 32 are formed on the substrate, separated by gaps 34. A central region 31 is located within the middle rectangular region 32.

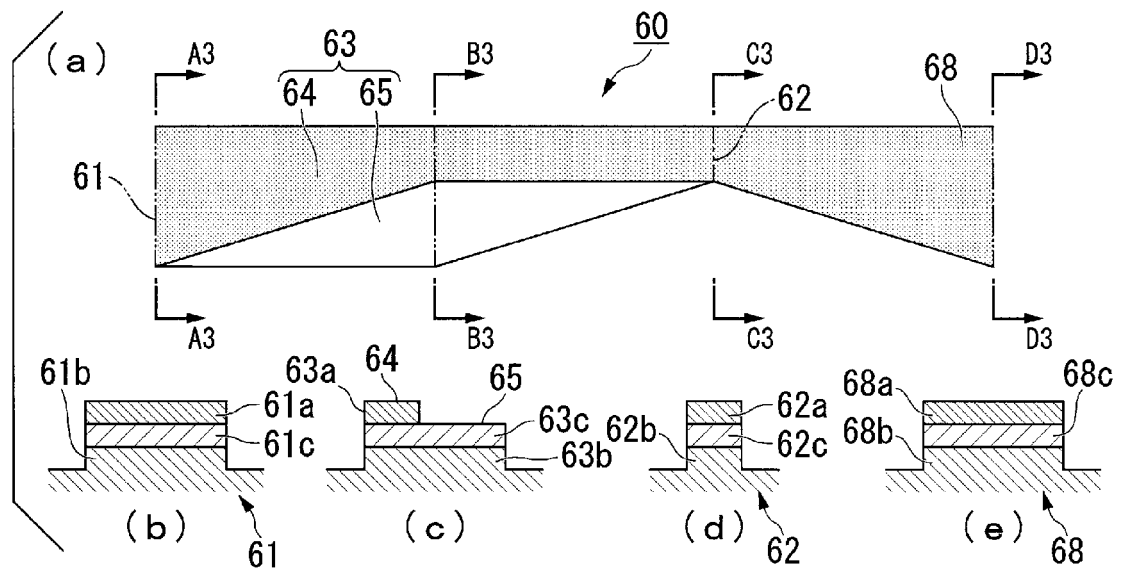
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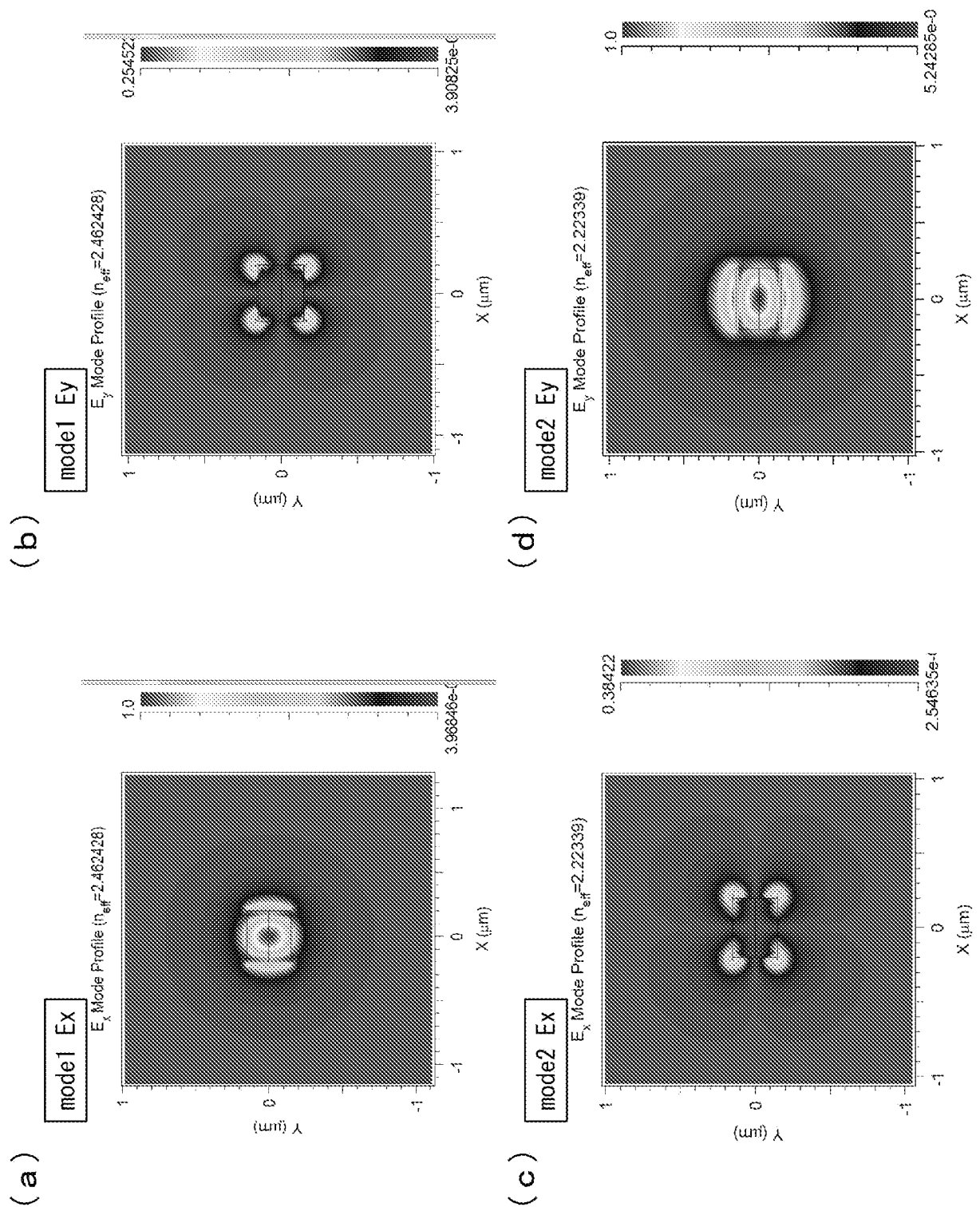
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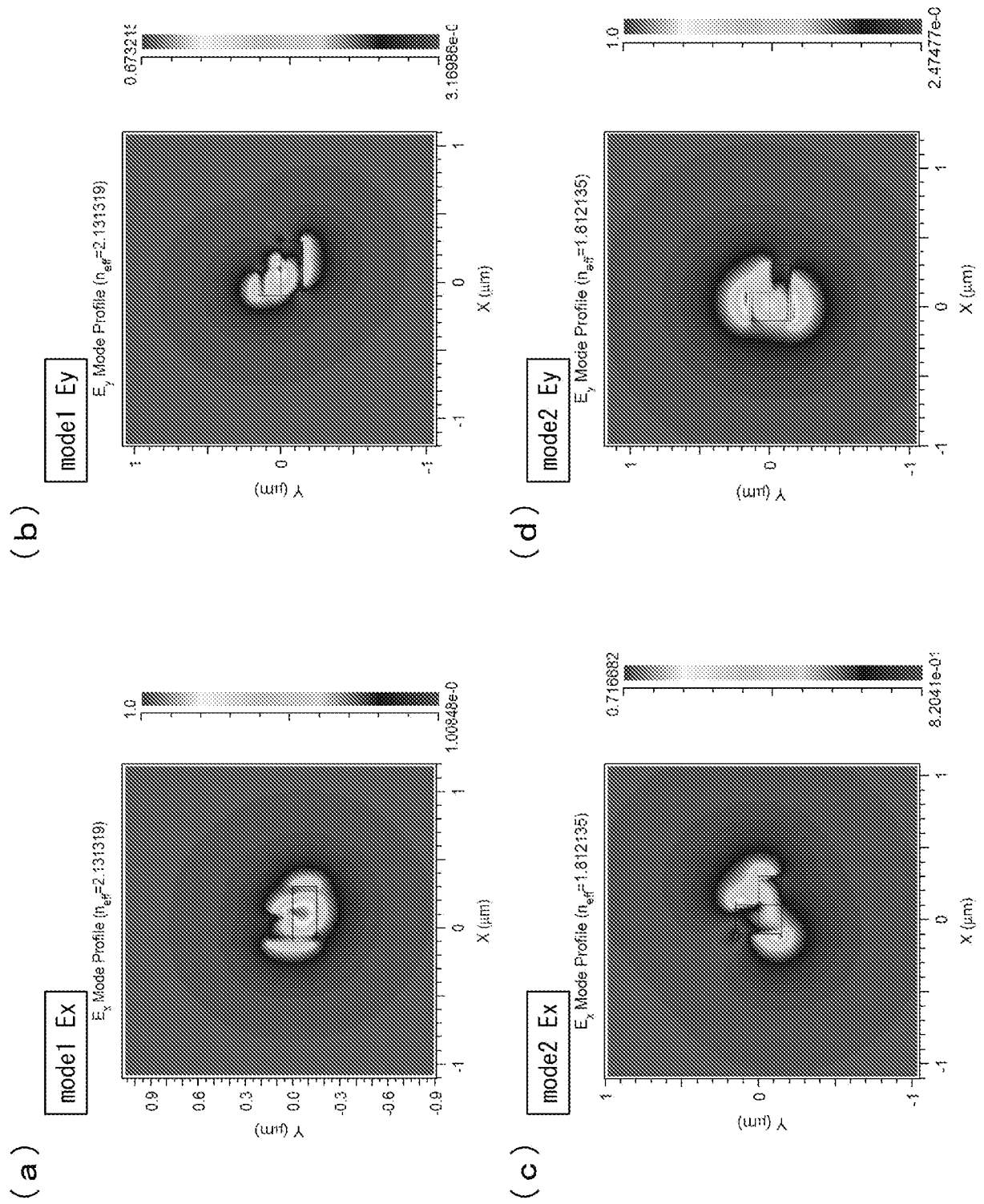
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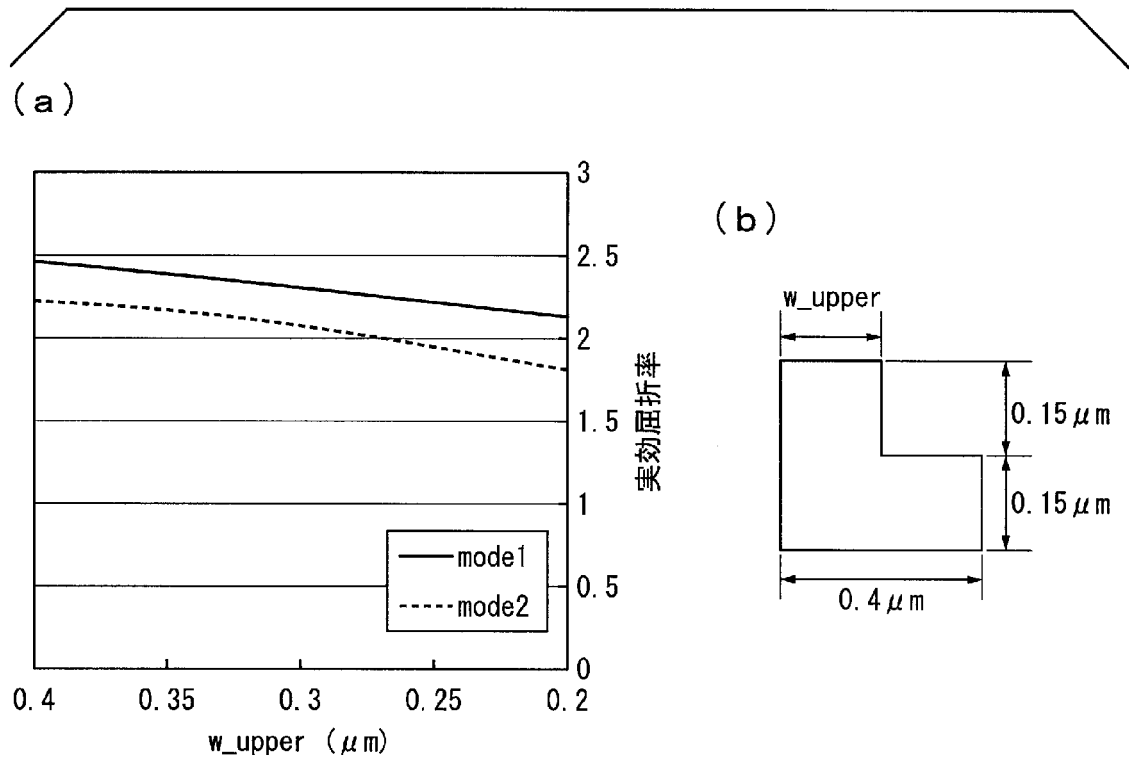
[図20]



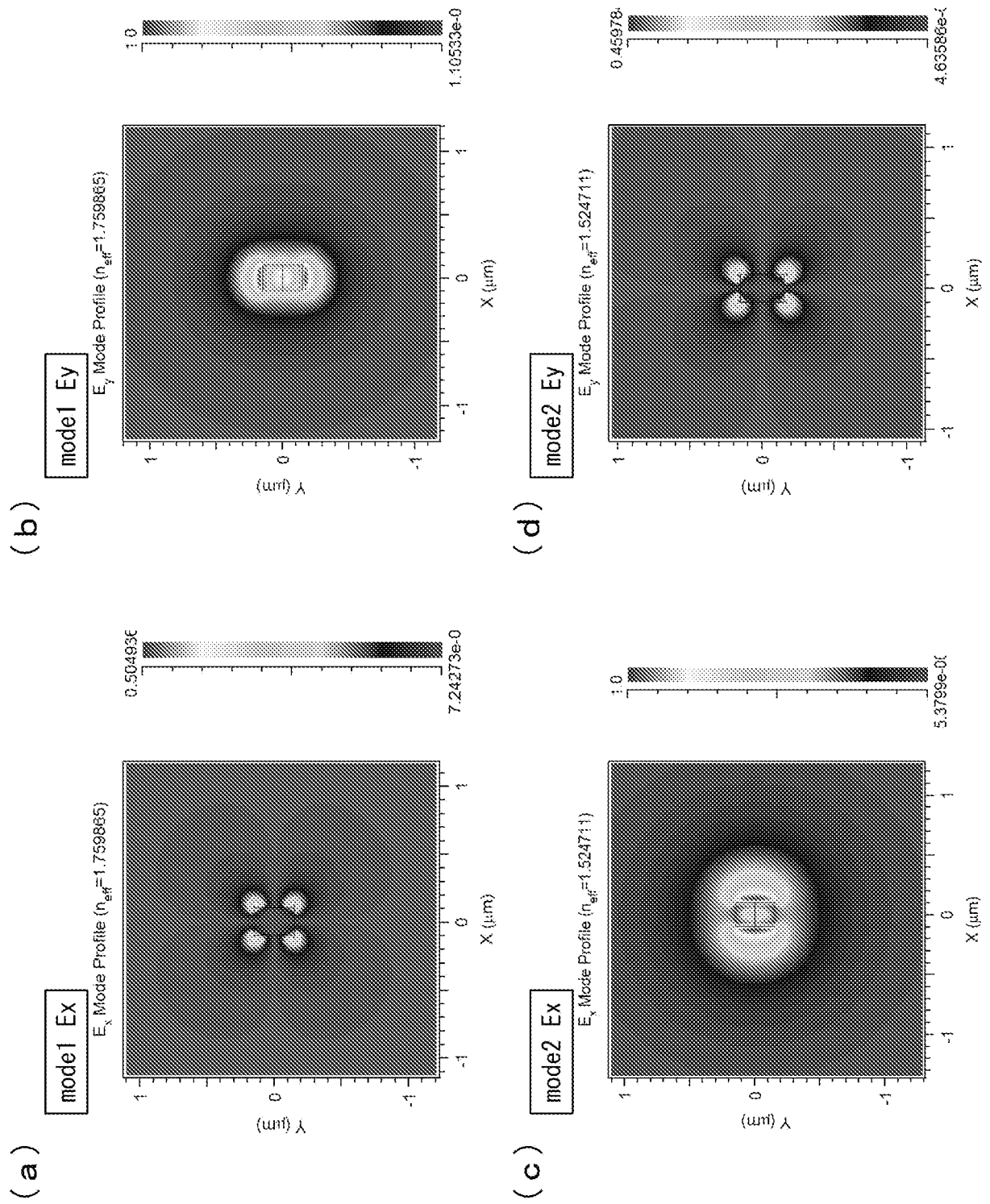
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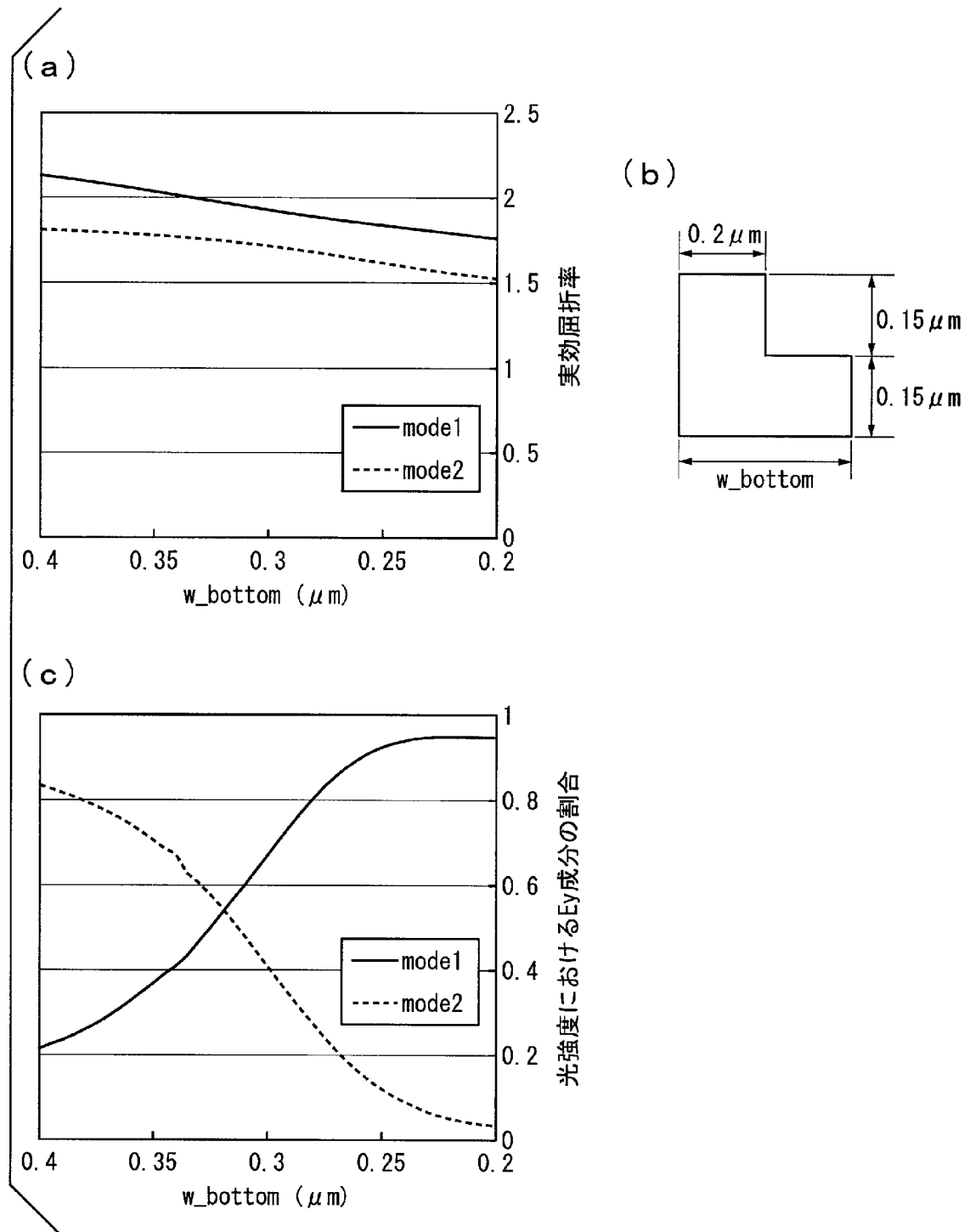
[図22]



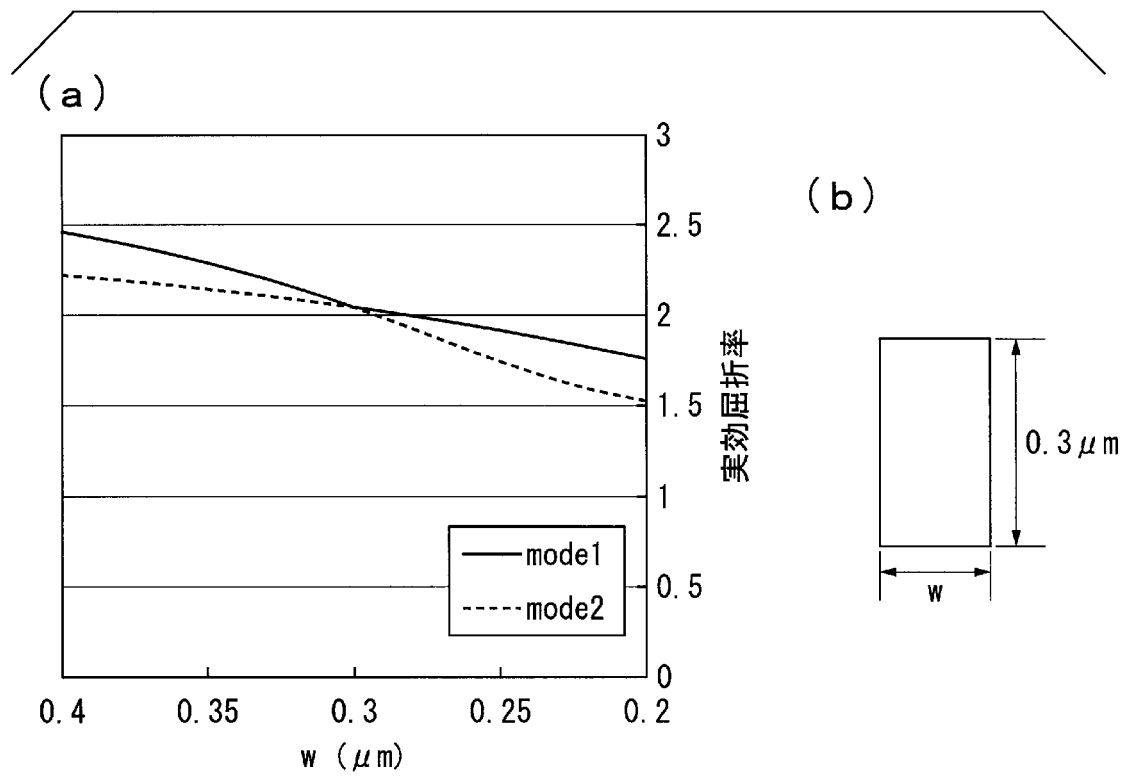
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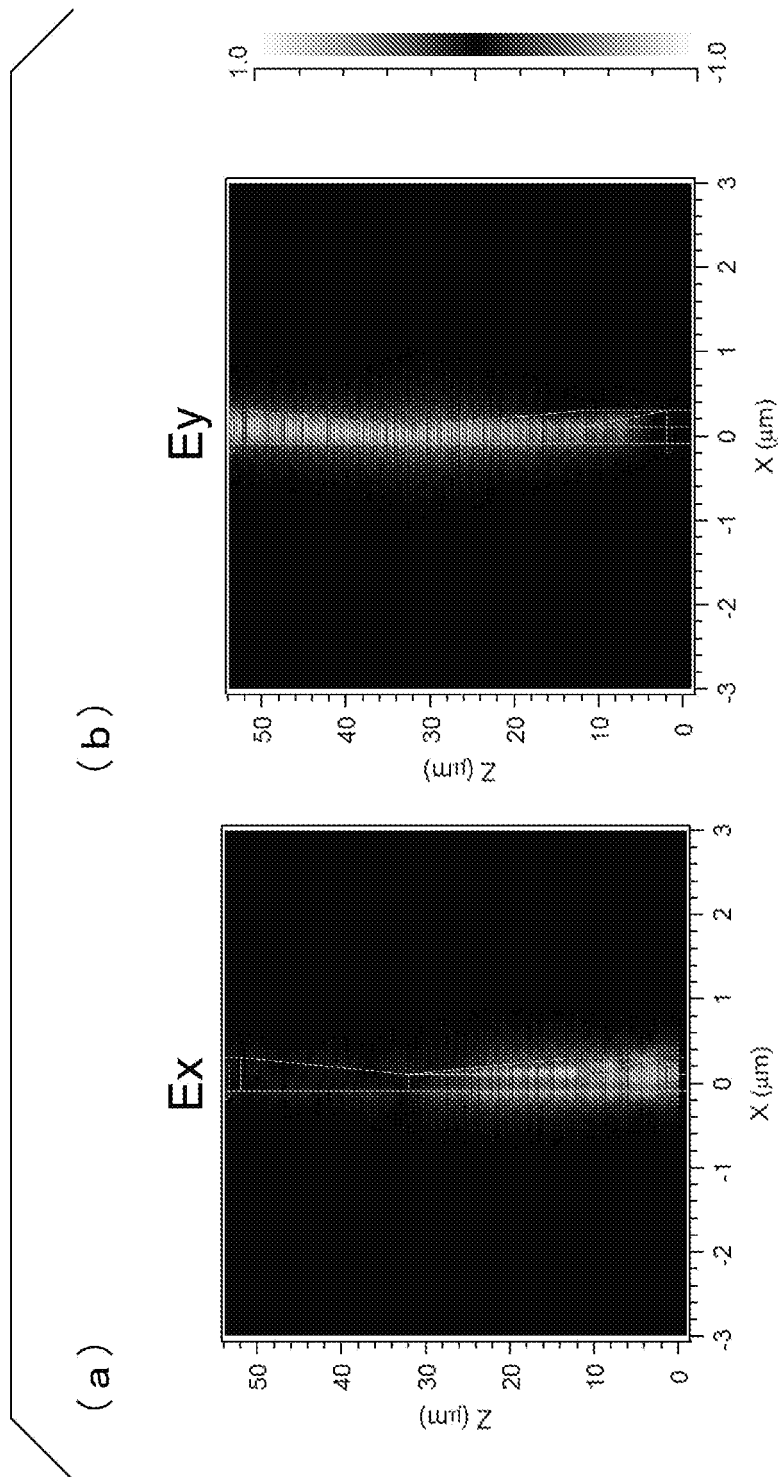
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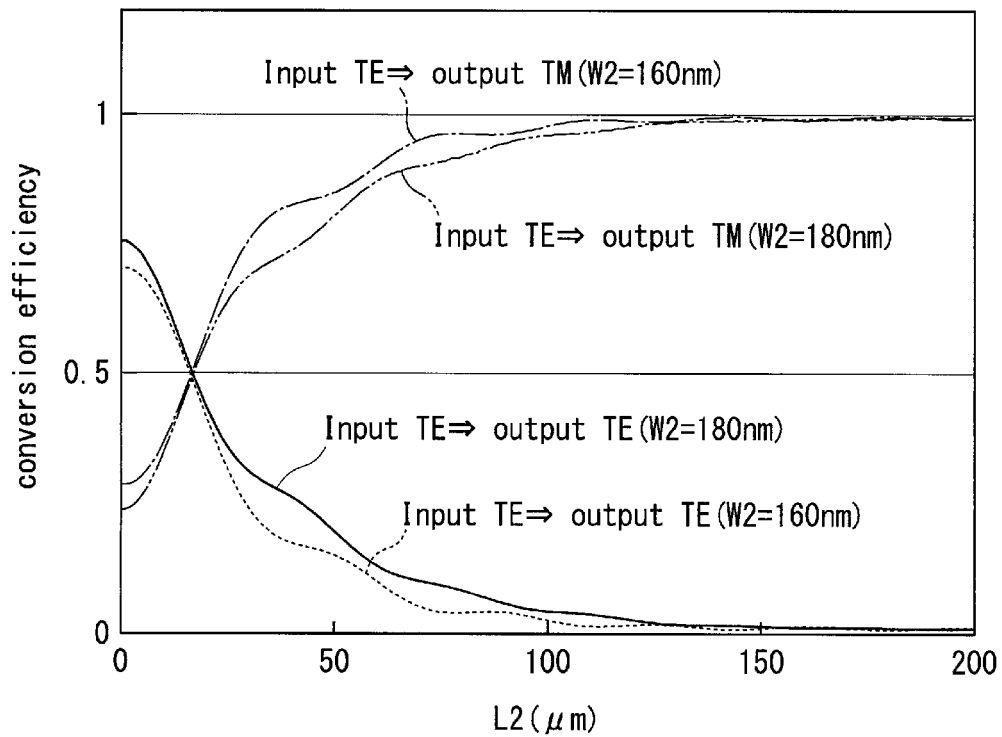
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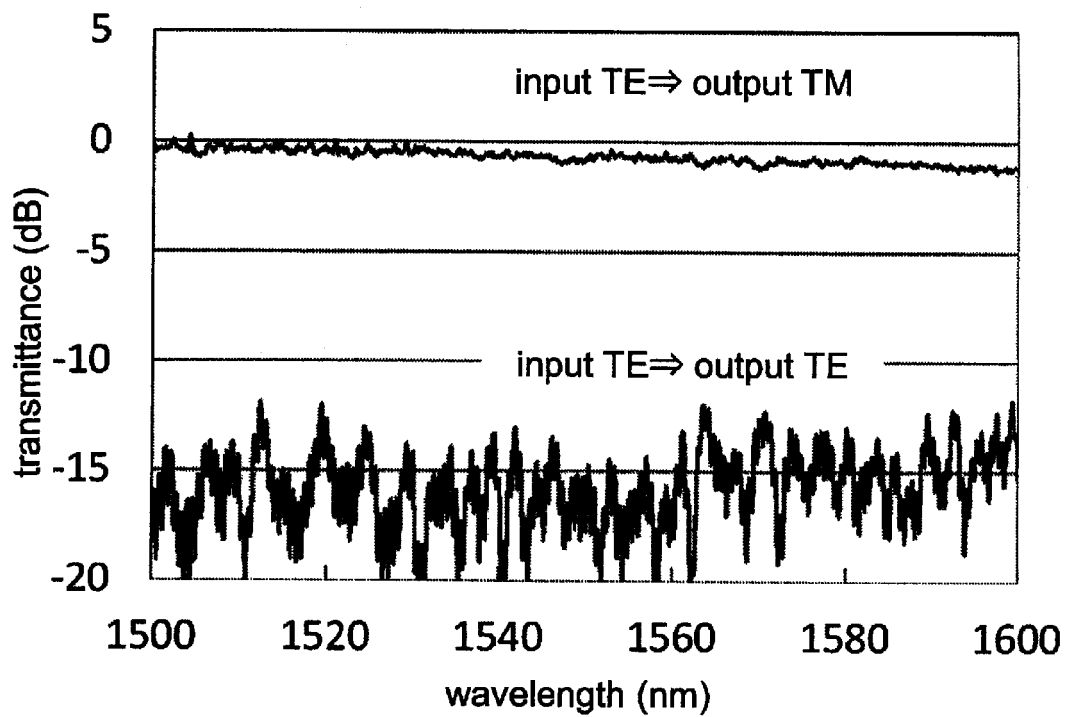
[図26]



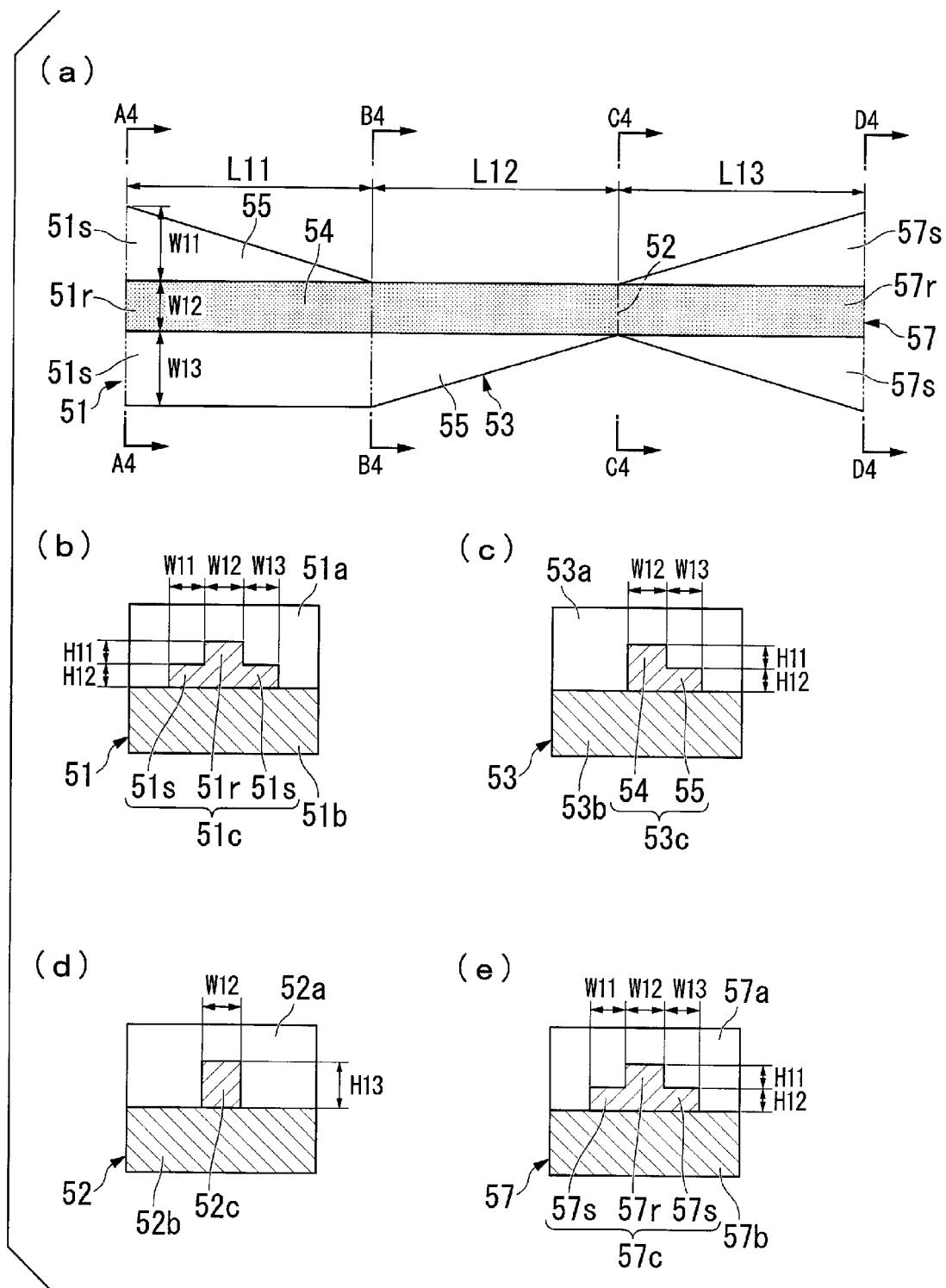
[図27]



[図28]

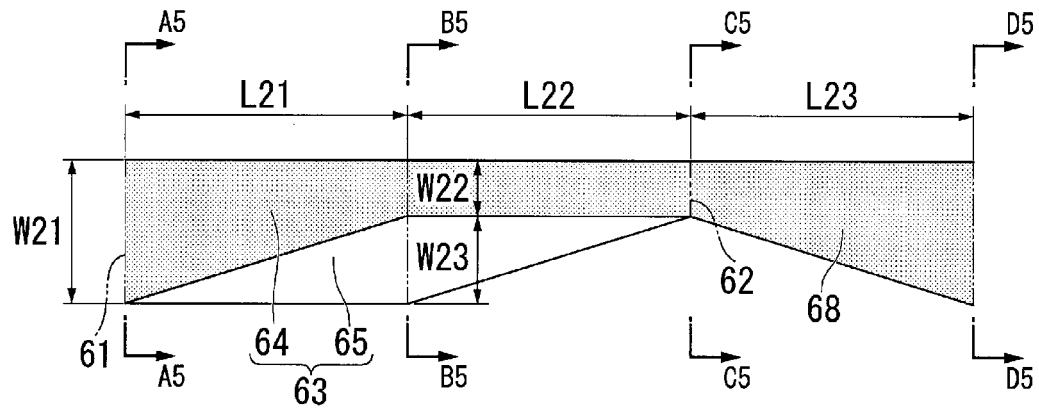


[図29]

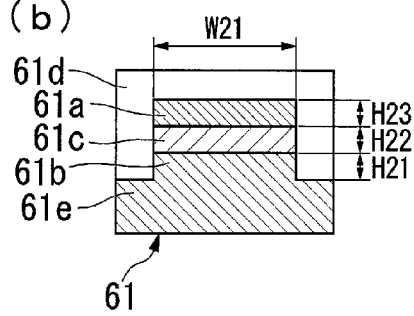


[図30]

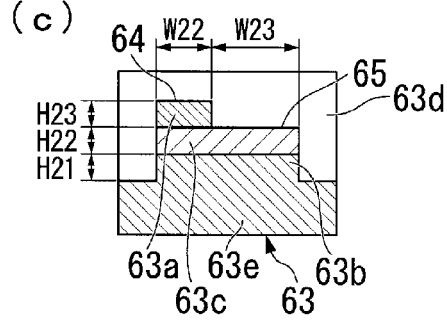
(a)



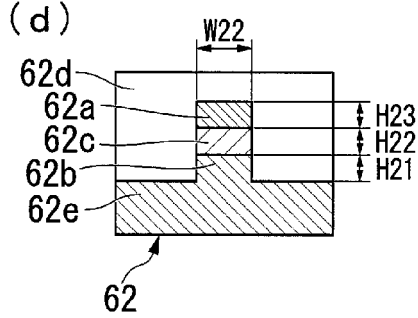
(b)



(c)



(d)



(e)

